

WLD-100-785-A/D Infrared Laser Diode
785 nm, 100 mW
Features

- Good FFP performance
- Higher power
- High efficiency
- Narrow wavelength: $785 \pm 2 \text{ nm}$

Applications

- Excitation
- Bioanalytical
- Photolithography, Curing and others

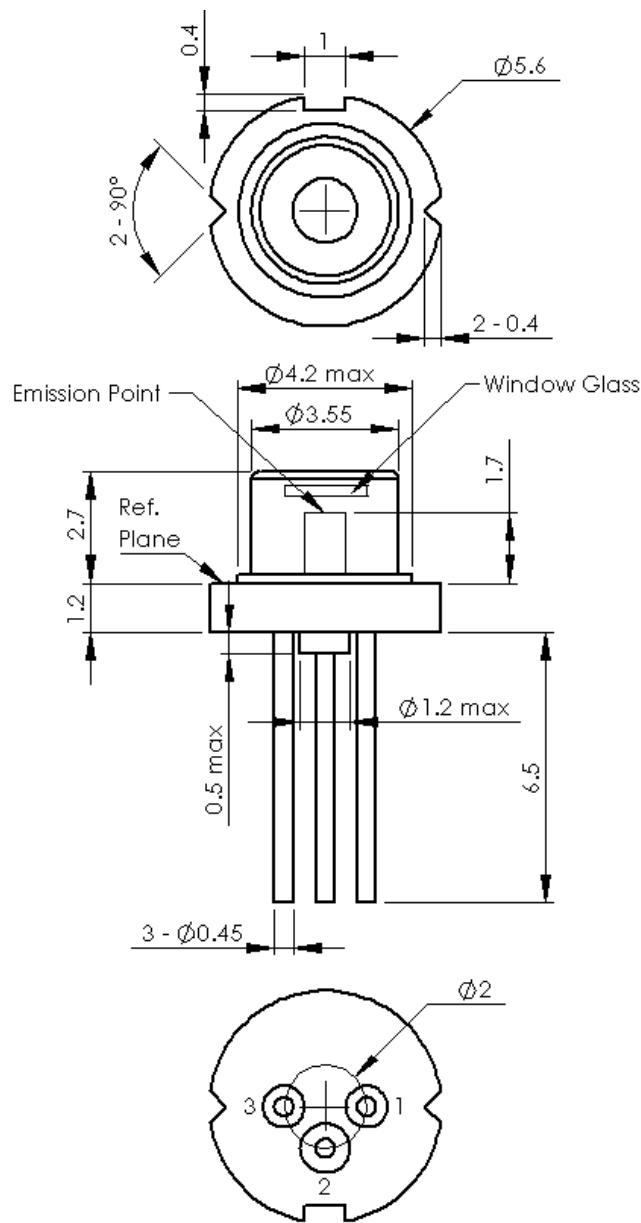
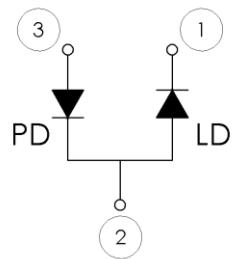
Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Light output power	P_0	CW	120	mW
Light output power	P_P	Pulse	280	mW
Reverse voltage (LD)	V_{RL}	-	2	V
Reverse voltage (PD)	V_{RD}	-	30	V
Case temperature	T_c	-	-10 to +70	°C
Storage temperature	T_s	-	-40 to +85	°C

Electrical and Optical Characteristics

Parameter	Symbol	Min	Typ.	Max	Unit	Condition
Threshold current	I_{th}	-	35	55	mA	-
Operating current	I_{op}	-	135	190	mA	$P_0=100 \text{ mW}$
Operating voltage	V_{op}	-	2.3	2.8	V	
Peak wavelength	λ	783	785	787	nm	
Parallel divergence angle	θ_{\parallel}	6	9	12	°	
Perpendicular divergence angle	θ_{\perp}	13	16	19	°	
Parallel FFP deviation angle	$\Delta\theta_{\parallel}$	-3	0	3	°	
Perpendicular FFP deviation angle	$\Delta\theta_{\perp}$	-3	0	3	°	
Differential efficiency	η	0.8	1.0	-	mW/mA	$\frac{100 \text{ mW}}{I(100) \text{ mW} - I(5) \text{ mW}}$



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